

N-channel 620 V, 0.95 Ω , 7.0 A Power MOSFET in D²PAK and in DPAK

Datasheet - production data

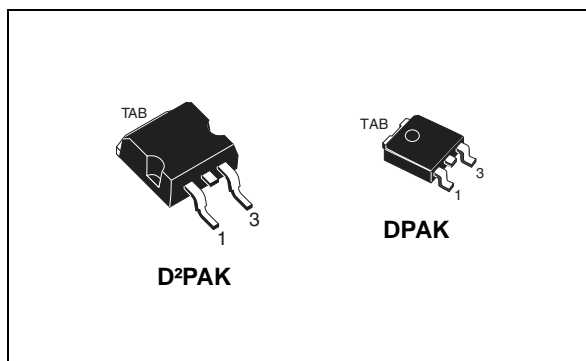
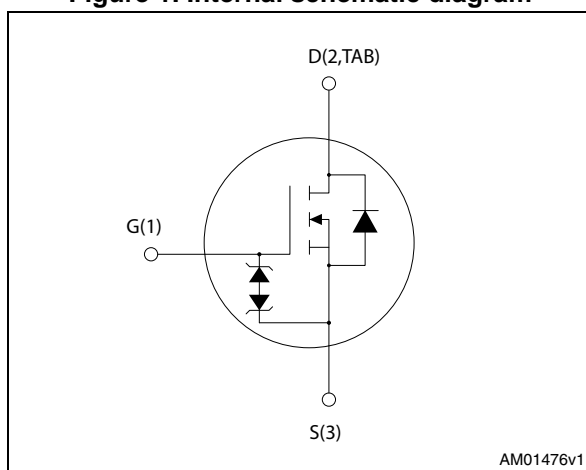


Figure 1. Internal schematic diagram



Features

Order codes	V _{DSS}	R _{DS(on)} max.	I _D	P _w
STBLED627	620 V	< 1.2 Ω	7.0 A	90 W
STDLED627				

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Applications

- LED lighting applications

Description

These Power MOSFETs boast extremely low on resistance and very good dv/dt capability, rendering them suitable for buck-boost and flyback topologies.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STBLED627	LED627	D ² PAK	Tape and reel
STDLED627		DPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK	DPAK	
V_{DS}	Drain-source voltage	620		V
V_{GS}	Gate-source voltage	± 30		V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	7.0		A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	4.0		A
$I_{DM}^{(1)}$	Drain current (pulsed)	28		A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	90		W
$I_{AR}^{(2)}$	Avalanche current, repetitive or not-repetitive	5.5		A
$E_{AS}^{(3)}$	Single pulse avalanche energy	140		mJ
ESD	Gate-source human body model ($R = 1.5\text{ k}\Omega$, $C = 100\text{ pF}$)	2.5		kV
$dv/dt^{(4)}$	Peak diode recovery voltage slope	12		V/ns
T_{stg}	Storage temperature	-55 to 150		°C
T_j	Max. operating junction temperature	150		°C

1. Pulse width limited by safe operating area.
2. Pulse width limited by T_j max.
3. Starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.
4. $I_{SD} \leq 5.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal data

Symbol	Parameter	D ² PAK	DPAK	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	1.39		°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max.	30	50	°C/W

1. When mounted on 1inch² FR-4 board, 2 oz Cu.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	620			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 620\text{ V}$ $V_{DS} = 620\text{ V}$, $T_C = 125\text{ °C}$			0.8 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 9	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.6	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.8\text{ A}$		0.95	1.2	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	890	-	pF pF pF
C_{oss}	Output capacitance		-	110	-	
C_{riss}	Reverse transfer capacitance		-	18	-	
$C_{oss(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0$, $V_{DS} = 0\text{ to }480\text{ V}$	-	28	-	pF
$C_{oss(tr)}^{(2)}$	Equivalent output capacitance time related		-	63	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	3.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 496\text{ V}$, $I_D = 5.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 18)	-	35	-	nC
Q_{gs}	Gate-source charge		-	4.5	-	nC
Q_{gd}	Gate-drain charge		-	23	-	nC

1. It is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .
2. It is defined as a constant equivalent capacitance giving the same storage energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 310\text{ V}$, $I_D = 2.75\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17)	-	22	-	ns
t_r	Rise time		-	12	-	ns
$t_{d(off)}$	Turn-off-delay time		-	49	-	ns
t_f	Fall time		-	20	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		5.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				27	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5.5\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 5.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 22)	-	290		ns
Q_{rr}	Reverse recovery charge		-	1900		nC
I_{RRM}	Reverse recovery current		-	13.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 5.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 22)	-	335		ns
Q_{rr}	Reverse recovery charge		-	2400		nC
I_{RR}	Reverse recovery current		-	14.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage ($I_D = 0$)	$I_{gs} = \pm 1\text{ mA}$	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK

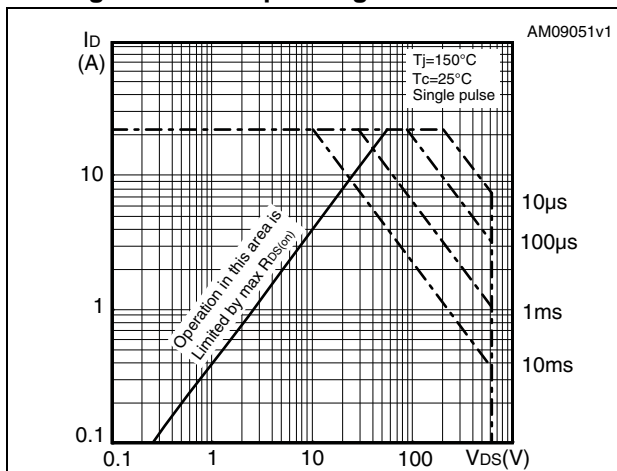


Figure 3. Thermal impedance for D²PAK

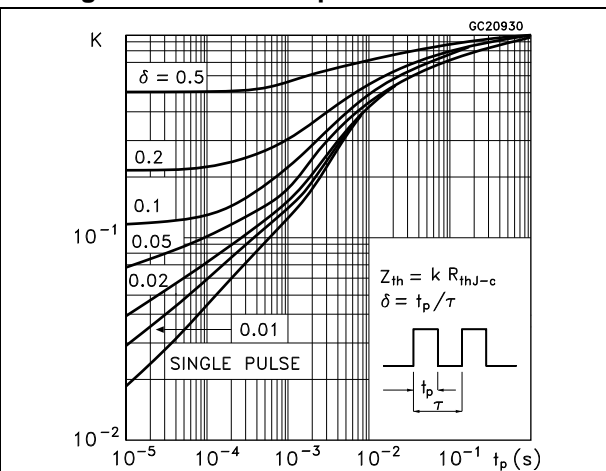


Figure 4. Safe operating area for DPAK

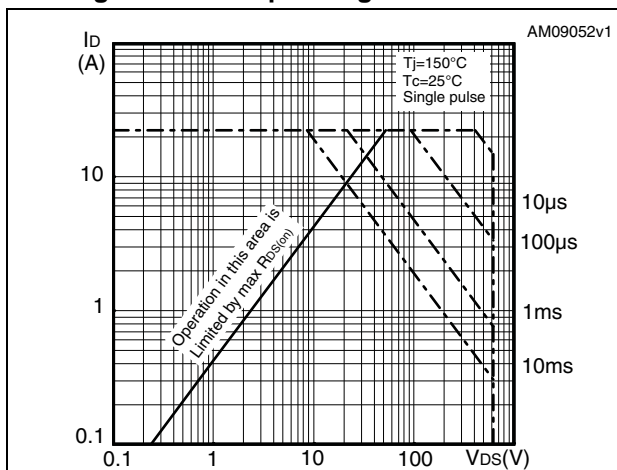


Figure 5. Thermal impedance for DPAK

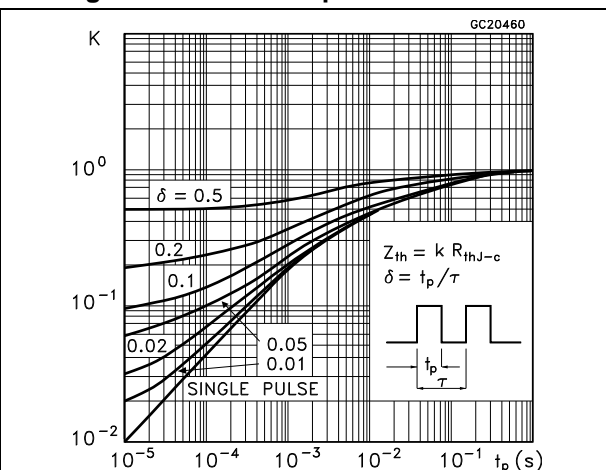


Figure 6. Output characteristics

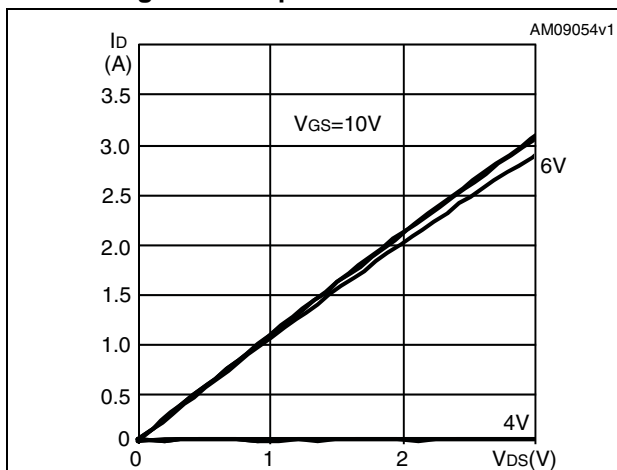


Figure 7. Transfer characteristics

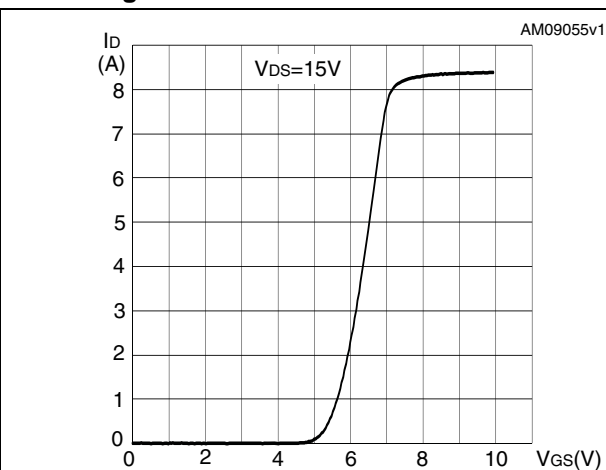


Figure 8. Gate charge vs gate-source voltage

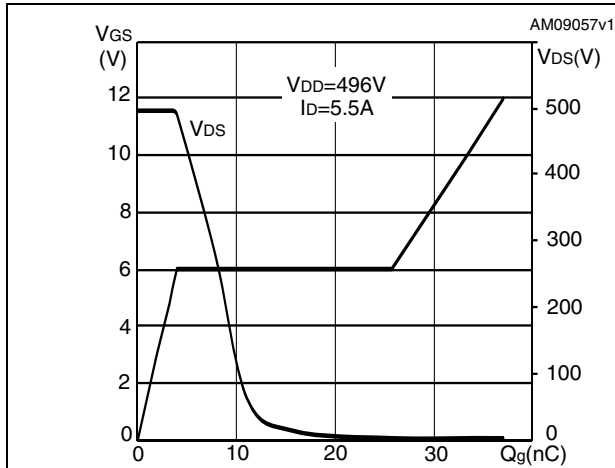


Figure 9. Static drain-source on-resistance

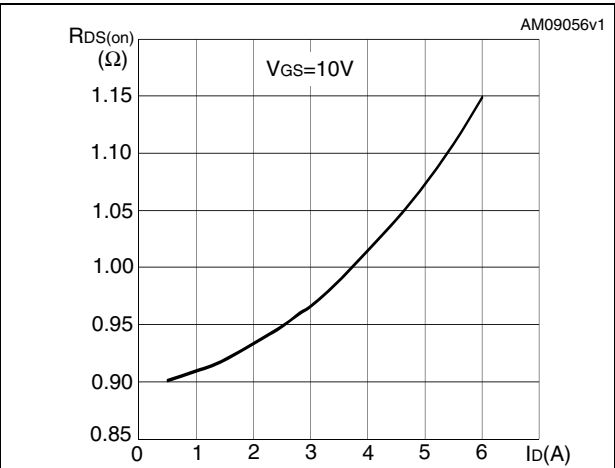


Figure 10. Capacitance variations

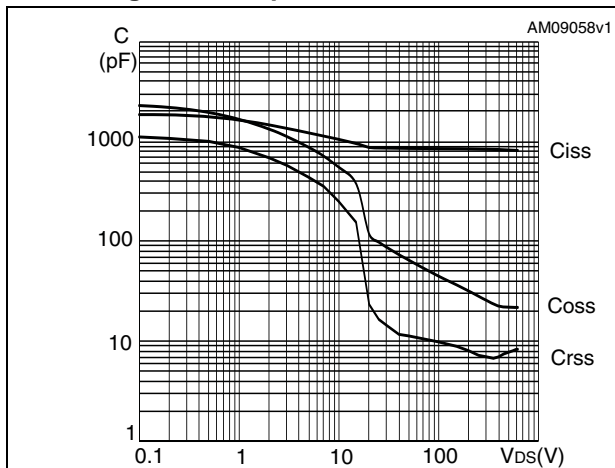


Figure 11. Output capacitance stored energy

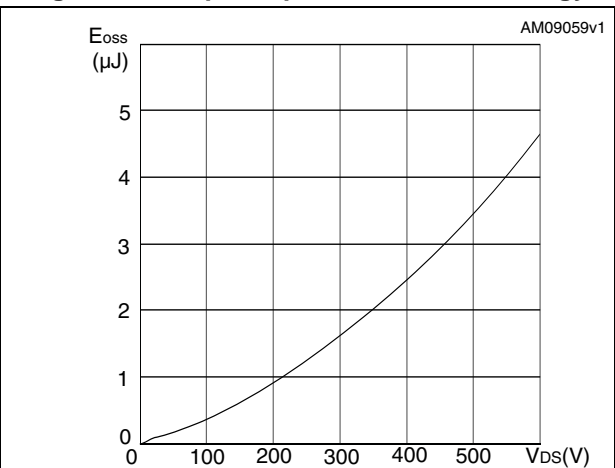


Figure 12. Normalized gate threshold voltage vs temperature

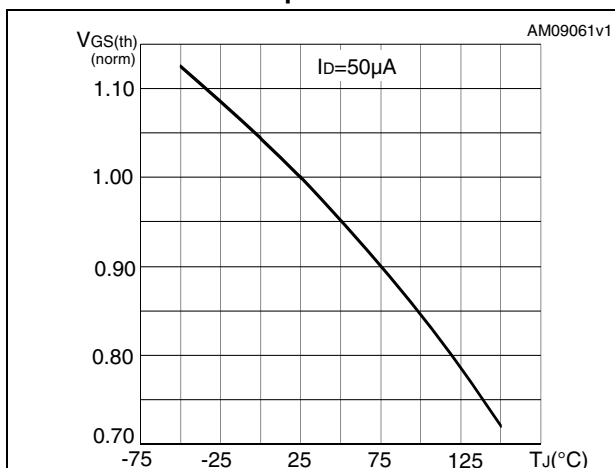


Figure 13. Normalized on-resistance vs temperature

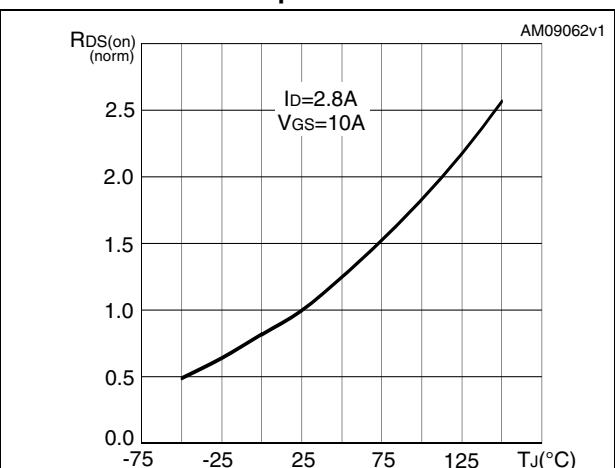


Figure 14. Normalized B_{VDSS} vs temperature

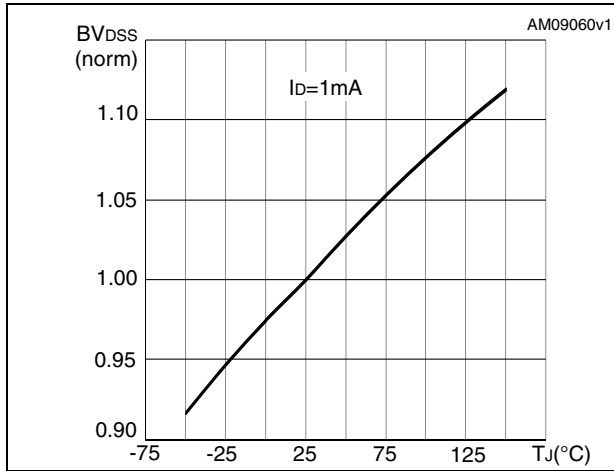


Figure 15. Source-drain diode forward characteristics

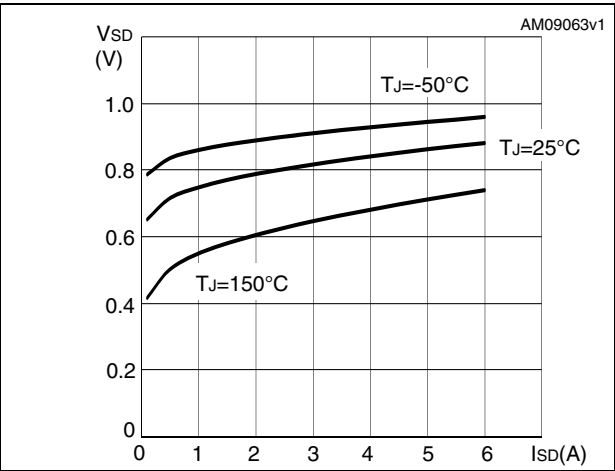
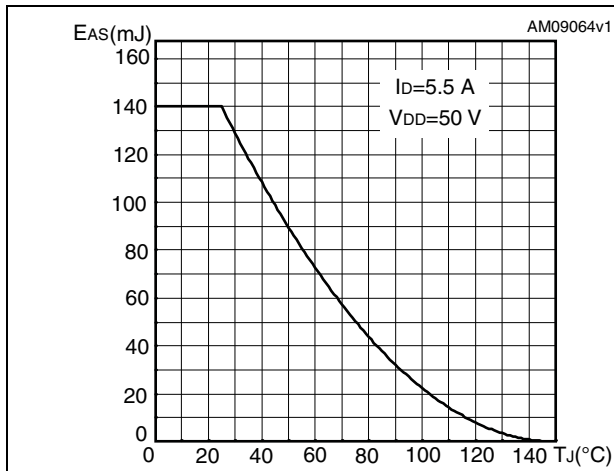


Figure 16. Maximum avalanche energy vs temperature



3 Test circuits

Figure 17. Switching times test circuit for resistive load

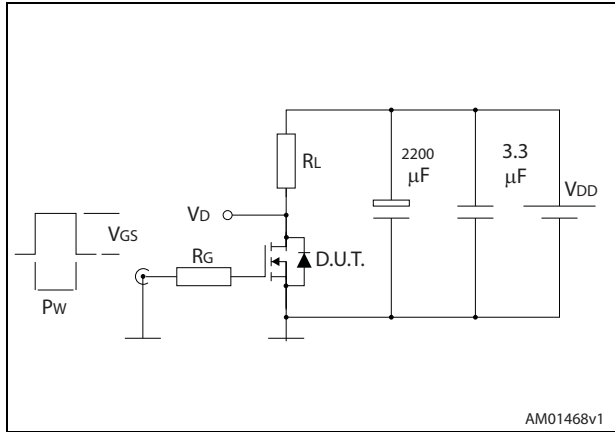


Figure 18. Gate charge test circuit

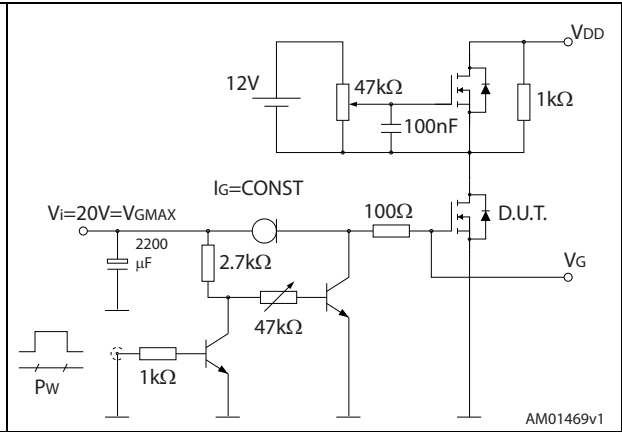


Figure 19. Test circuit for inductive load switching and diode recovery times

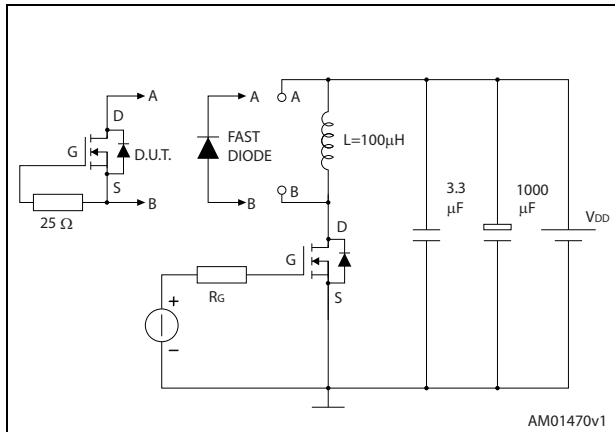


Figure 20. Unclamped Inductive load test circuit

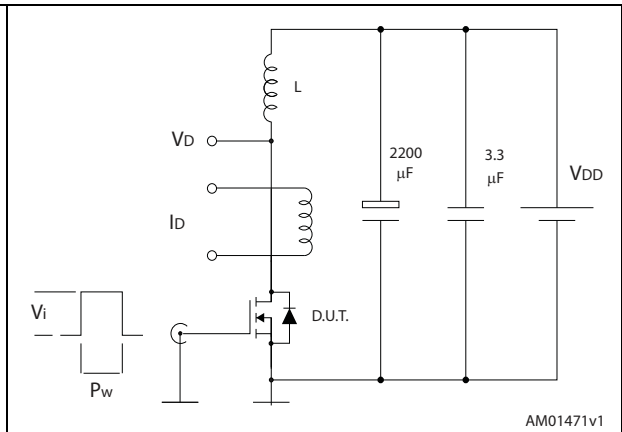


Figure 21. Unclamped inductive waveform

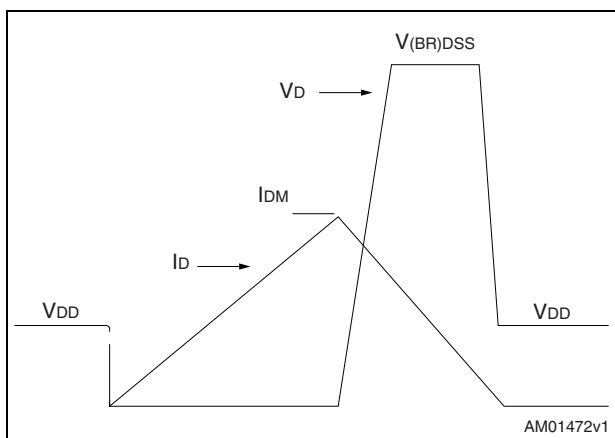
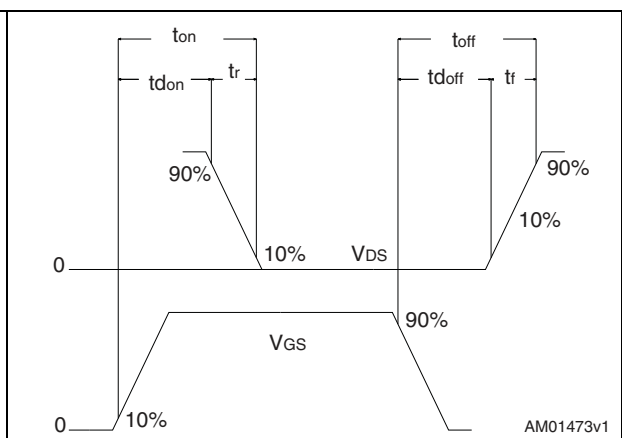


Figure 22. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 23. D²PAK (TO-263) drawings

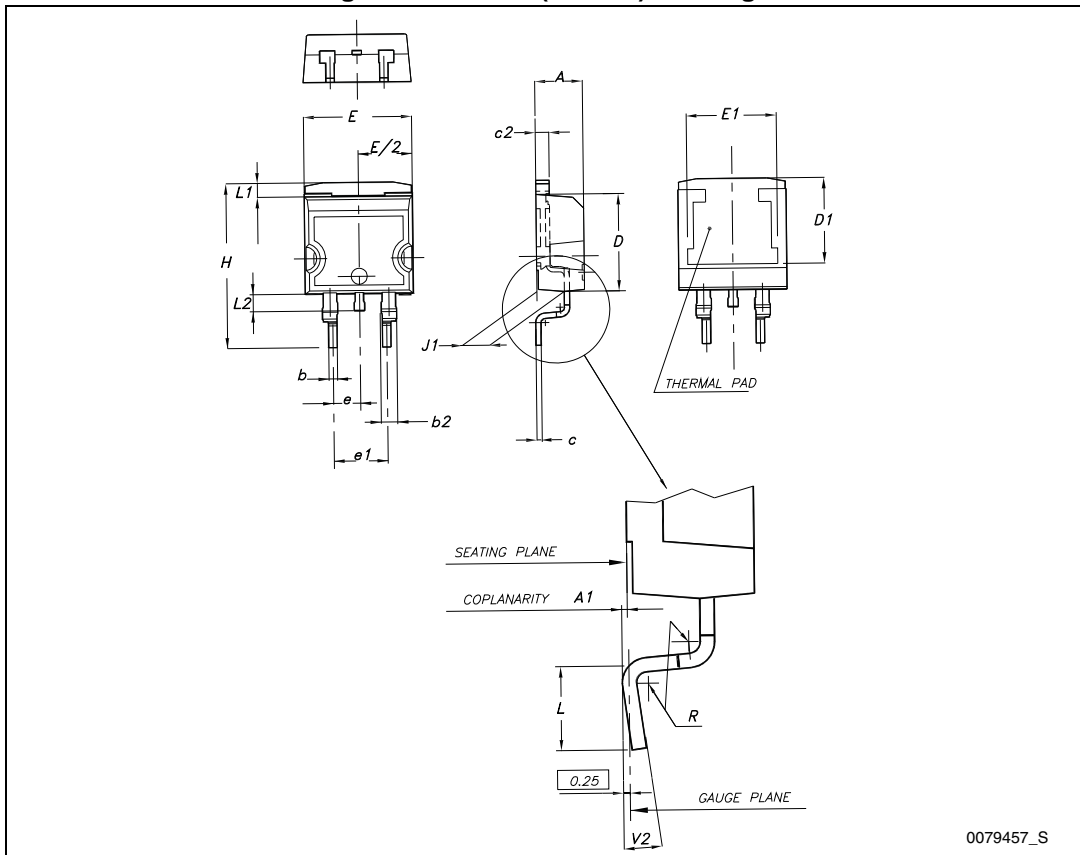
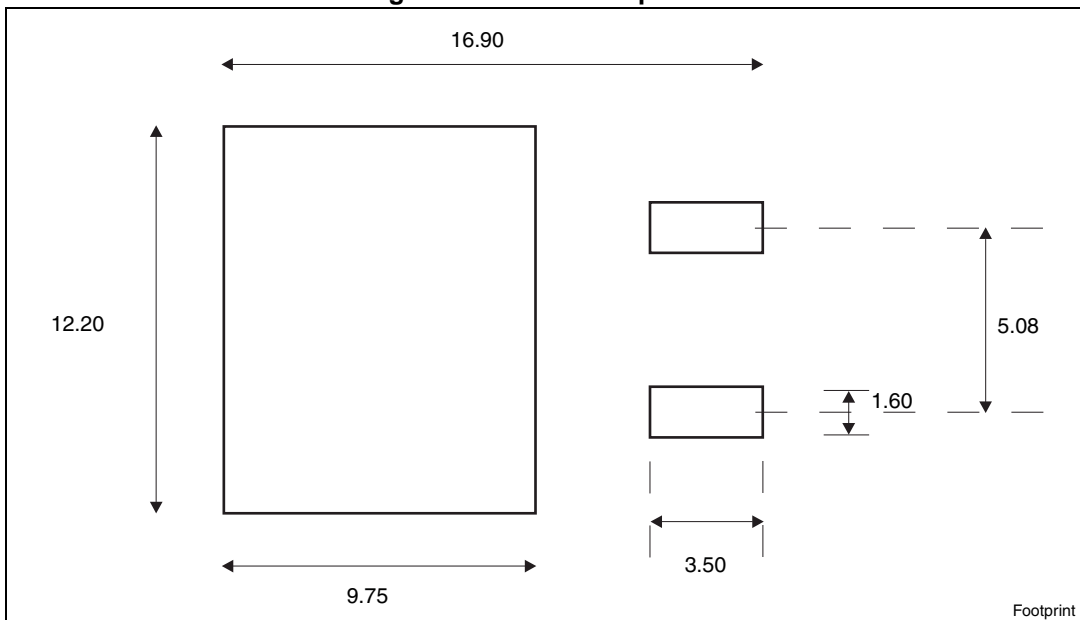


Figure 24. D²PAK footprint^(a)



a. All dimensions are in millimeters.

Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 25. DPAK (TO-252) drawings

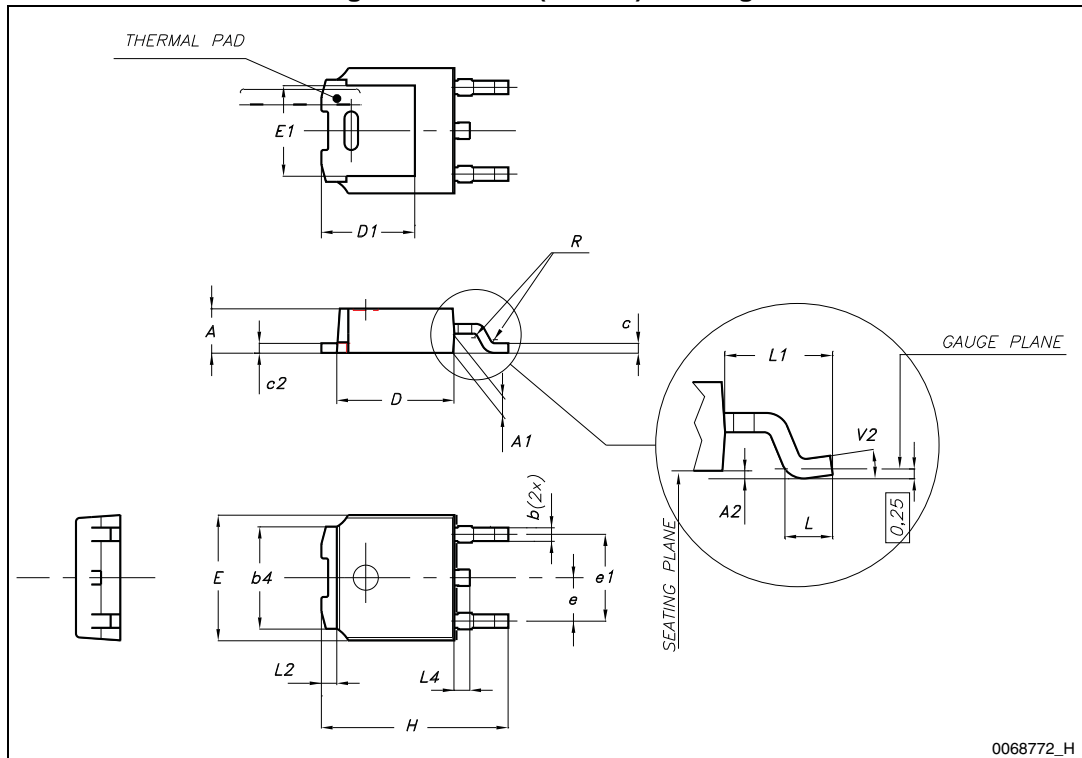
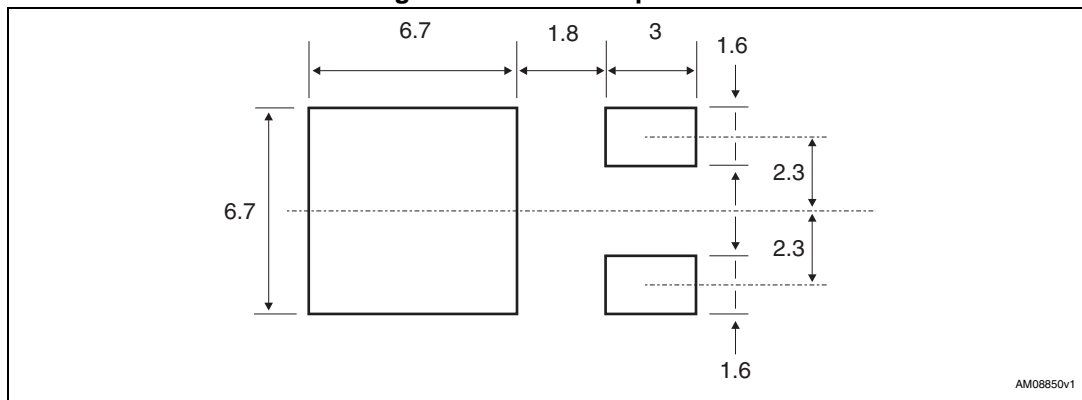


Figure 26. DPAK footprint^(b)



b. All dimensions are in millimeters.

5 Packaging mechanical data

Table 11. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Table 12. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 27. Tape for DPAK (TO-252) and D²PAK (TO-263)

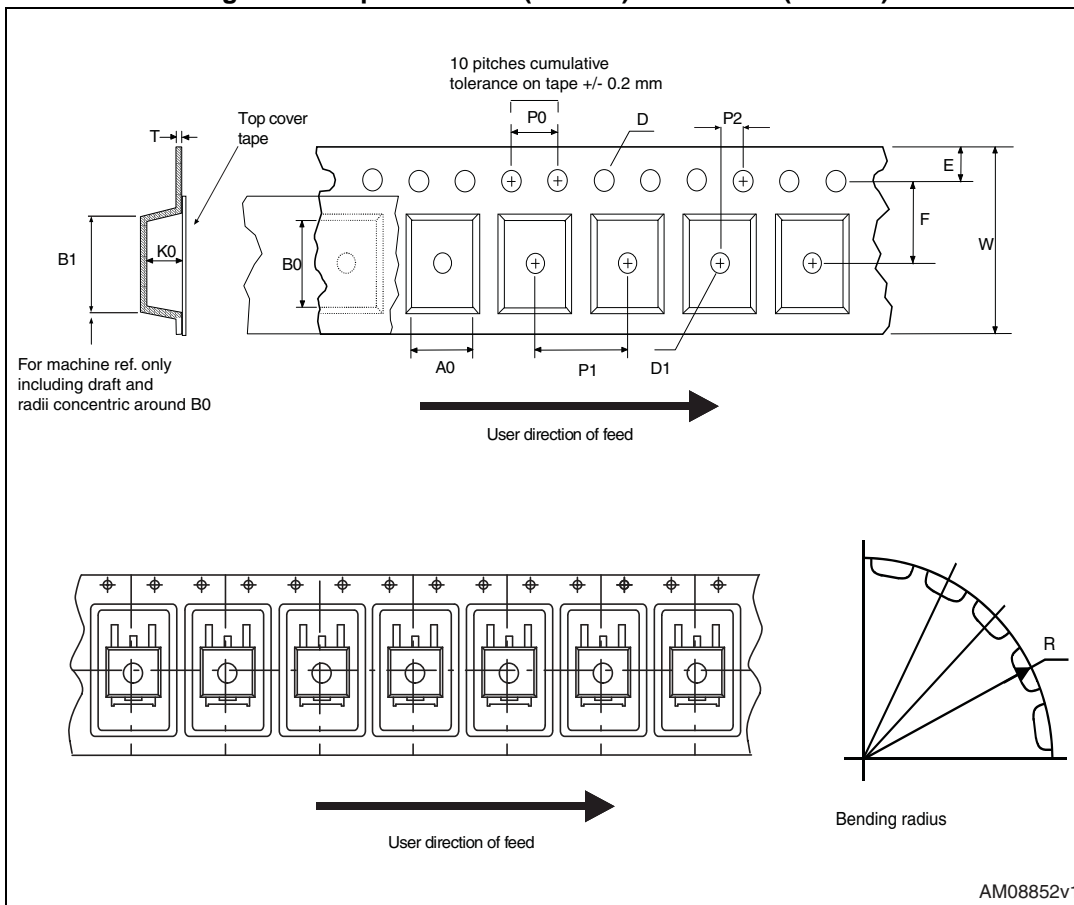
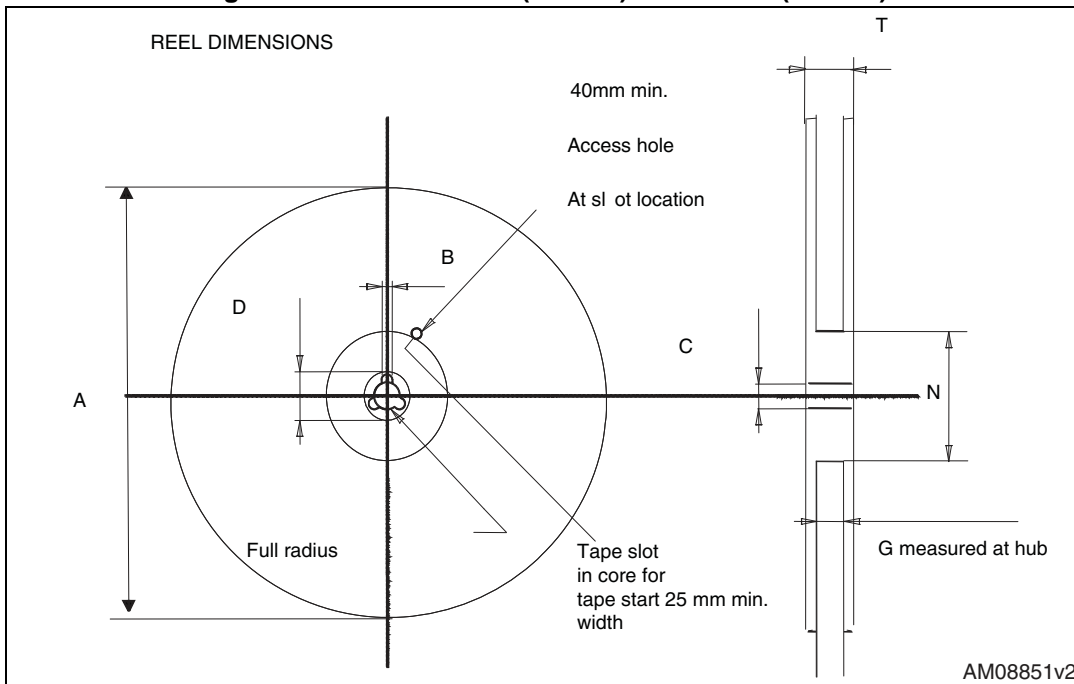


Figure 28. Reel for DPAK (TO-252) and D²PAK (TO-263)



6 Revision history

Table 13. Document revision history

Date	Revision	Changes
29-Aug-2013	1	First release.

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